

## Product Summary

BV <sub>DSS</sub>	R <sub>Ds(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
40V	3.6mΩ @ V <sub>GS</sub> = 10V	100A
	5.2mΩ @ V <sub>GS</sub> = 5V	90A

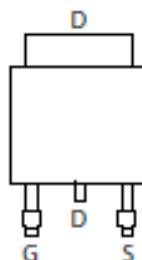
## Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>Ds(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

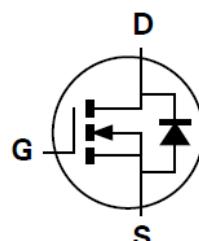
- Power Management Functions
- DC-DC Converters
- Backlighting



Top View



Pin Out Top View



Equivalent Circuit

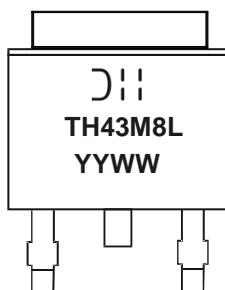
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH43M8LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



DII = Manufacturer's Marking  
TH43M8L = Product Type Marking Code  
YYWW = Date Code Marking  
YY = Last Two Digits of Year (ex: 17 = 2017)  
WW = Week Code (01 to 53)

**Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	40	V	
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V	
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)	$T_A = +25^\circ\text{C}$ $T_A = +100^\circ\text{C}$	$I_D$	17.6 12.5	A
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	$T_C = +25^\circ\text{C}$ $T_C = +100^\circ\text{C}$	$I_D$	100 80	A
Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{DM}$	150	A	
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	70	A	
Pulsed Body Diode Forward Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)	$I_{SM}$	150	A	
Avalanche Current, $L=1\text{mH}$	$I_{AS}$	13.2	A	
Avalanche Energy, $L=1\text{mH}$	$E_{AS}$	87	mJ	

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	$P_D$	88	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	1.7	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
<b>OFF CHARACTERISTICS</b> (Note 7)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	40	—	—	V	$V_{GS} = 0\text{V}, I_D = 1\text{mA}$	
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1	$\mu\text{A}$	$V_{DS} = 32\text{V}, V_{GS} = 0\text{V}$	
Gate-Source Leakage	$I_{GSS}$	—	—	$\pm 100$	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	
<b>ON CHARACTERISTICS</b> (Note 7)							
Gate Threshold Voltage	$V_{GS(\text{TH})}$	1	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	2.9	3.6	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	4.3	5.2	$\text{m}\Omega$	$V_{GS} = 5\text{V}, I_D = 15\text{A}$	
Diode Forward Voltage	$V_{SD}$	—	—	1.2	V	$V_{GS} = 0\text{V}, I_S = 20\text{A}$	
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)							
Input Capacitance	$C_{ISS}$	—	2,693	—	pF	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	
Output Capacitance	$C_{OSS}$	—	1,172	—			
Reverse Transfer Capacitance	$C_{RSS}$	—	52	—			
Gate Resistance	$R_G$	—	2.54	—	$\Omega$	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	
Total Gate Charge ( $V_{GS} = 10\text{V}$ )	$Q_G$	—	38.5	—	$\text{nC}$	$V_{DS} = 20\text{V}, I_D = 20\text{A}$	
Total Gate Charge ( $V_{GS} = 4.5\text{V}$ )	$Q_G$	—	17.6	—	$\text{nC}$		
Gate-Source Charge	$Q_{GS}$	—	6.9	—			
Gate-Drain Charge	$Q_{GD}$	—	6.9	—	$\text{ns}$	$V_{DD} = 20\text{V}, V_{GS} = 10\text{V}, I_D = 20\text{A}, R_G = 1.6\Omega$	
Turn-On Delay Time	$t_{D(\text{ON})}$	—	5.2	—			
Turn-On Rise Time	$t_R$	—	5.7	—			
Turn-Off Delay Time	$t_{D(\text{OFF})}$	—	23.5	—			
Turn-Off Fall Time	$t_F$	—	11	—	$\text{ns}$	$I_F = 15\text{A}, \text{di}/\text{dt} = 100\text{A}/\mu\text{s}$	
Body Diode Reverse Recovery Time	$t_{RR}$	—	35.4	—			
Body Diode Reverse Recovery Charge	$Q_{RR}$	—	32.9	—	$\text{nC}$		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

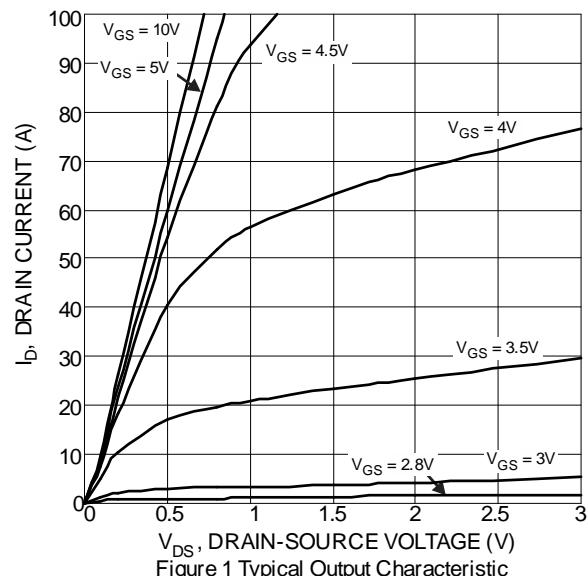


Figure 1 Typical Output Characteristic

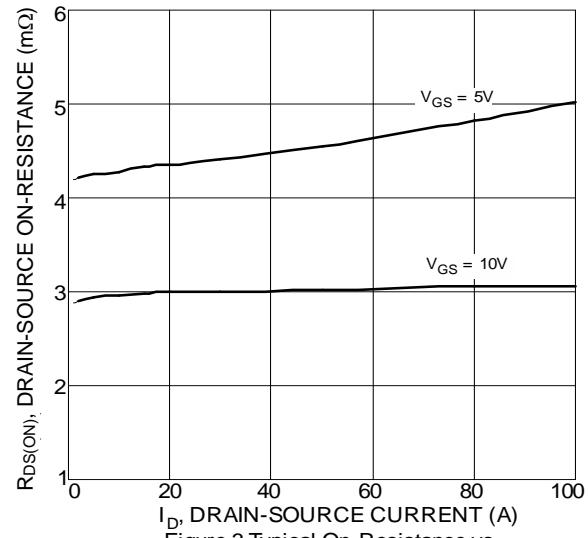


Figure 3 Typical On-Resistance vs.  
Drain Current and Gate Voltage

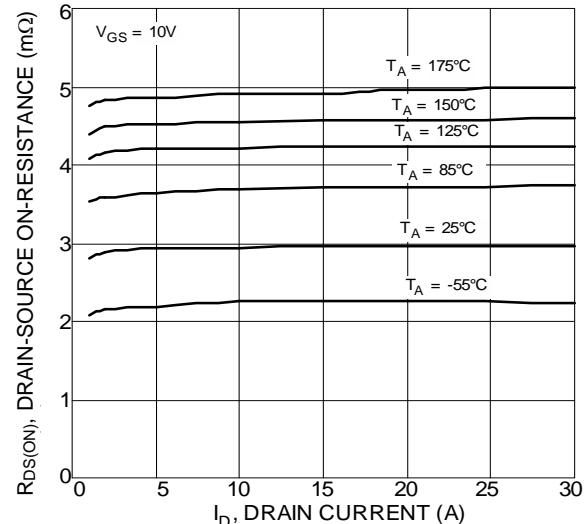


Figure 5 Typical On-Resistance vs.  
Drain Current and Temperature

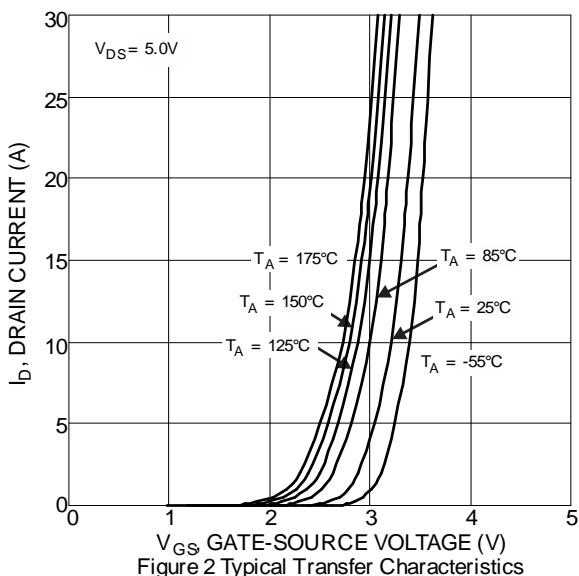


Figure 2 Typical Transfer Characteristics

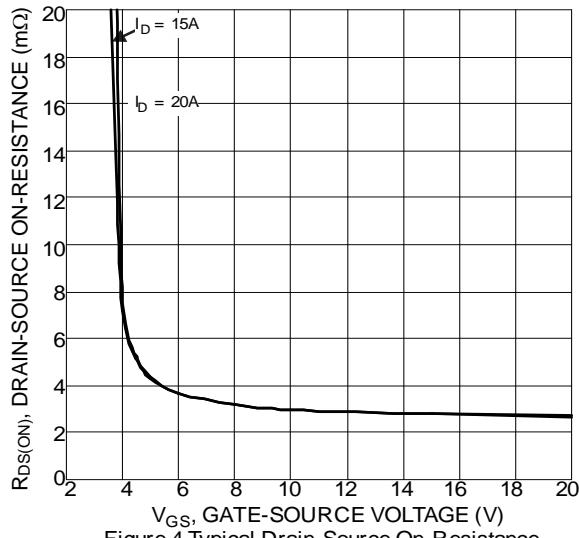


Figure 4 Typical Drain-Source On-Resistance  
vs. Gate-Source Voltage

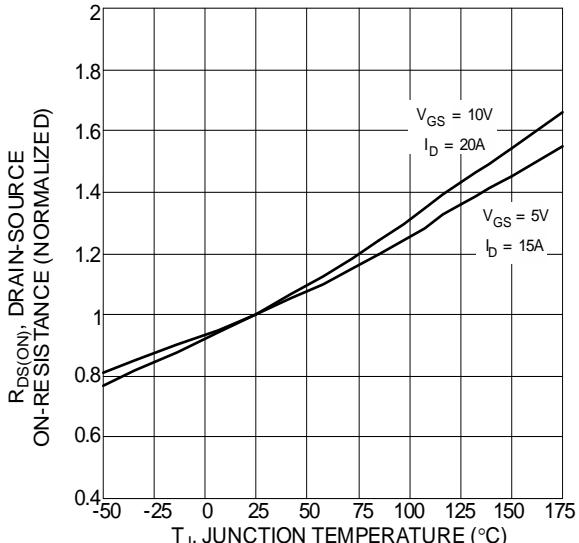
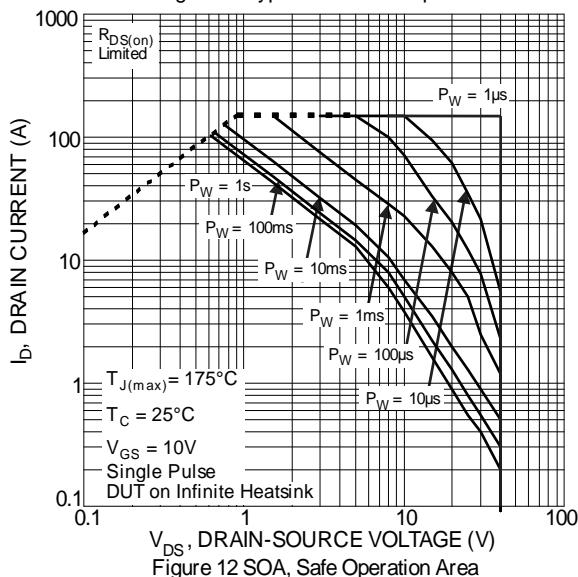
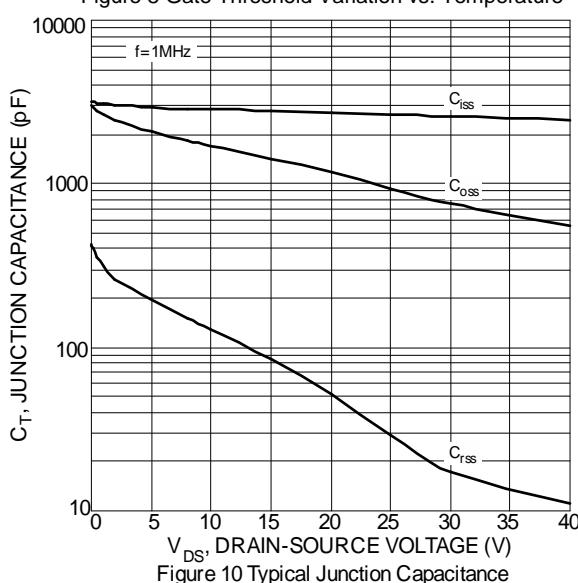
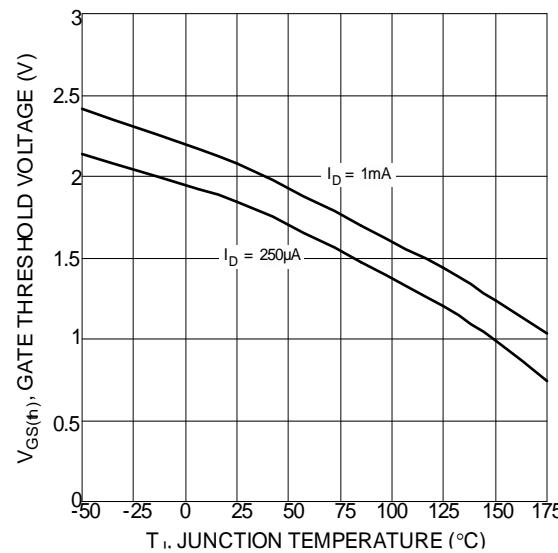
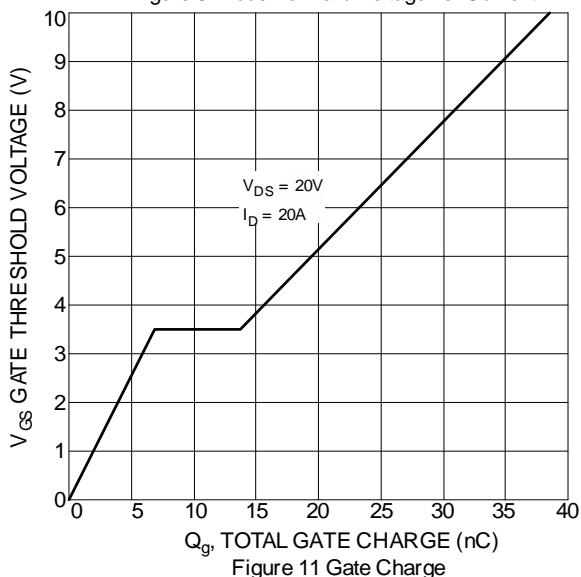
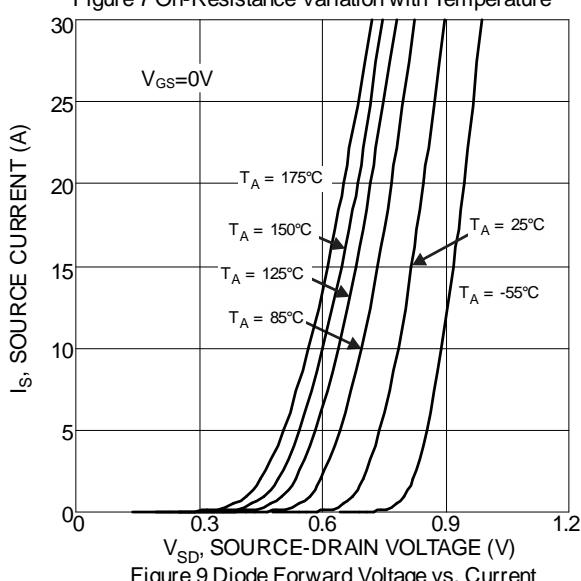
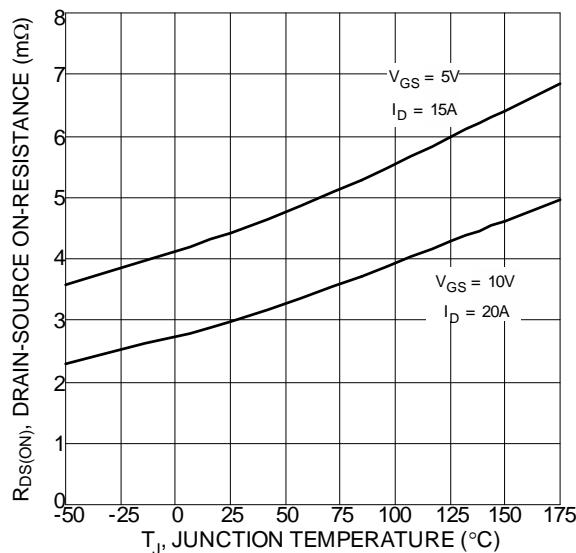


Figure 6 On-Resistance Variation with Temperature



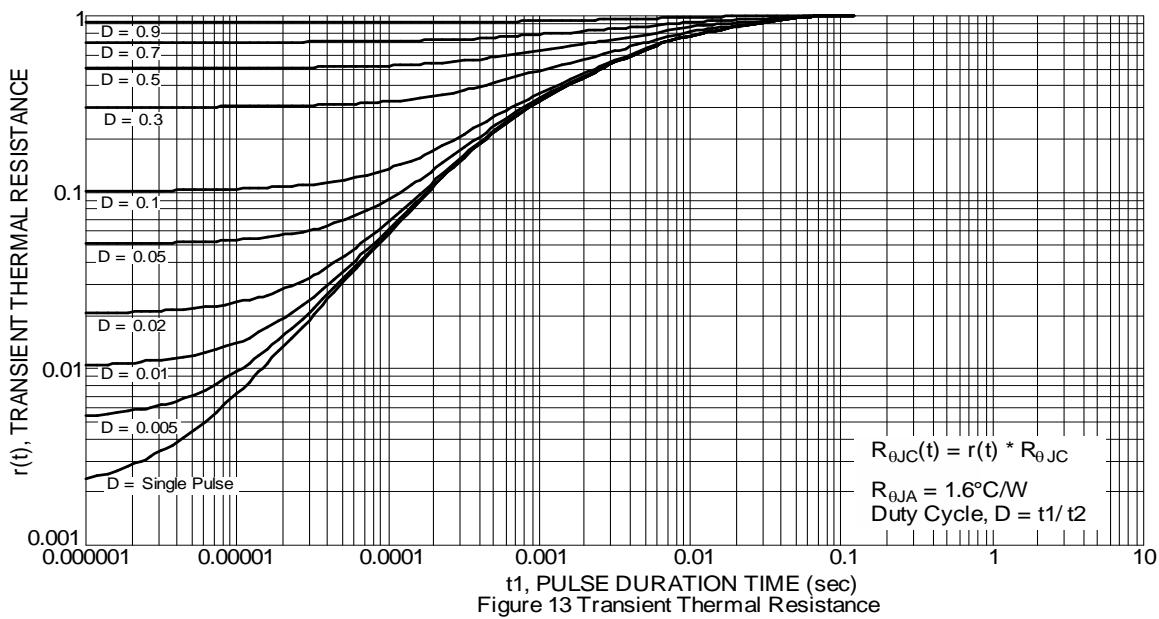
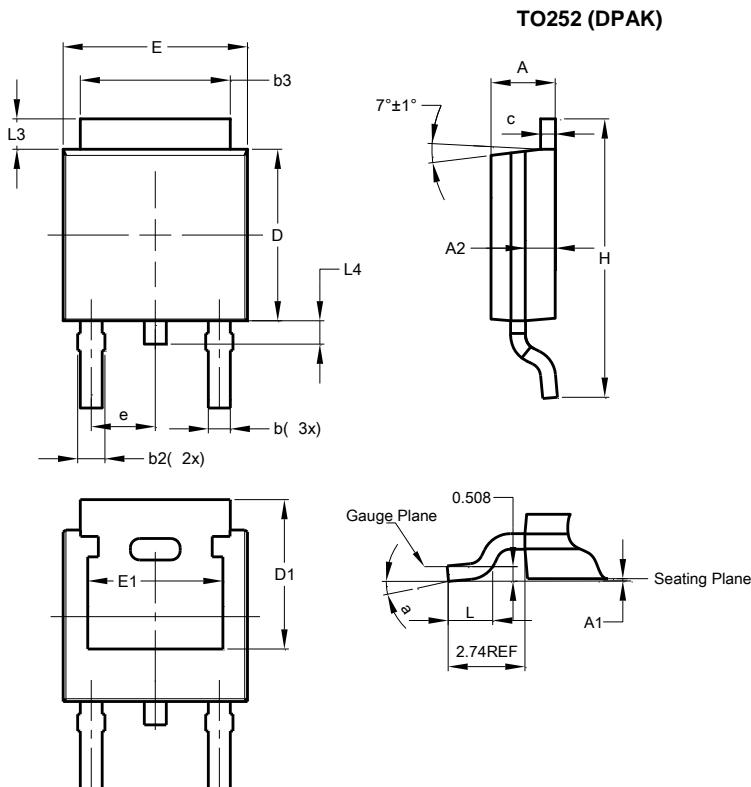


Figure 13 Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

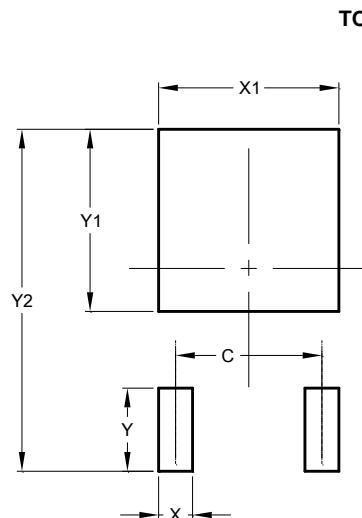


TO252 (DPAK)			
Dim	Min	Max	Typ
<b>A</b>	2.19	2.39	2.29
<b>A1</b>	0.00	0.13	0.08
<b>A2</b>	0.97	1.17	1.07
<b>b</b>	0.64	0.88	0.783
<b>b2</b>	0.76	1.14	0.95
<b>b3</b>	5.21	5.46	5.33
<b>c</b>	0.45	0.58	0.531
<b>D</b>	6.00	6.20	6.10
<b>D1</b>	5.21	-	-
<b>e</b>	-	-	2.286
<b>E</b>	6.45	6.70	6.58
<b>E1</b>	4.32	-	-
<b>H</b>	9.40	10.41	9.91
<b>L</b>	1.40	1.78	1.59
<b>L3</b>	0.88	1.27	1.08
<b>L4</b>	0.64	1.02	0.83
<b>a</b>	0°	10°	-

**All Dimensions in mm**

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
<b>C</b>	4.572
<b>X</b>	1.060
<b>X1</b>	5.632
<b>Y</b>	2.600
<b>Y1</b>	5.700
<b>Y2</b>	10.700

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